What is claimed is

1. An integrated sputtering target comprising a target portion and a backing plate portion, both of them being made of copper and unavoidable impurities,

wherein a Vickers hardness Hv is 90 or more, and wherein a flat ratio of crystal grains in a cross section orthogonal to a sputtering surface to be used for sputtering is 0.35 or more and 0.65 or less.

2. The sputtering target according to claim 1, wherein the sputtering target has an average crystal grain size of 10 μm or more and 60 μm or less.

3. The sputtering target according to claim 1 or 2, wherein the target portion and the backing plate portion contain one or more elements selected from the group consisting of Fe, Cr, Ni, Si, Ag, S and P in a total amount of 0.01% by mass or less as the unavoidable impurities.

4. A method for manufacturing an integrated sputtering target comprising a target portion and a backing plate portion, both of them being made of copper and unavoidable impurities, the method comprising:

melting a raw material to cast an ingot comprising copper and unavoidable impurities; and subjecting the ingot to hot forging, first cold rolling or first cold forging, a heat treatment, and second cold rolling or second cold forging in this order,

wherein the second cold rolling or the second cold forging is carried out at a change rate of from 20% to 40%,

wherein in the second cold rolling or the second cold forging, crystal grains is crushed in a thickness direction to change a flat ratio of the crystal grains in a cross section orthogonal to a sputtering surface to be used for sputtering,

and wherein the heat treatment is carried out at a temperature of from 200 °C to 500 °C for 0.5 hours to 3 hours.

5. The method according to claim 4, wherein the first cold rolling or the first cold forging is carried out at a change rate of 70% or more.

6. The method according to claim 4 or 5 wherein the hot forging is carried out at a temperature of from 300 °C to 900 °C.

7. The method according to any one of claims 4 to 6, wherein the ingot contains one or more elements selected from the group consisting of Fe, Cr, Ni, Si, Ag, S, and P in a total amount of 0.01% mass or less as the unavoidable impurities.

8. An integrated sputtering target comprising a target portion and a backing plate portion, both of them containing from 0.1% by mass to 8% by mass of at least one element selected from aluminum, manganese, nickel and cobalt, the balance being copper and unavoidable impurities,

wherein a Vickers hardness Hv is 90 or more, and wherein a flat ratio of crystal grains in a cross section orthogonal to a sputtering surface to be used for sputtering is 0.35 or more and 0.85 or less.

9. The sputtering target according to claim 8, wherein the sputtering target has an average crystal grain size of 5 μm or more and 50 μm or less.

10. The sputtering target according to claim 8 or 9, wherein the target portion and the backing plate portion contain one or more elements selected from the group consisting of Fe, Cr, Si, Ag, S and P in a total amount of 0.01% by mass or less as the unavoidable impurities.

11. The sputtering target according to any one of claims 8 to 10, wherein the sputtering target contains from 0.1% by mass to 6% by mass of at least one element selected from aluminum, manganese, nickel and cobalt.

12. A method for manufacturing an integrated sputtering target comprising a target portion and a backing plate portion, both of them containing from 0.1% by mass to 8% by mass of at least one element selected from aluminum, manganese, nickel and cobalt, the balance being copper and the inevitable impurities, the method comprising:

melting a raw material to cast an ingot comprising the element, copper and the unavoidable impurities; and subjecting the ingot to hot forging, first cold rolling or first cold forging, a heat treatment, and a second cold rolling or a second cold forging in this order,

wherein the second cold rolling or the second cold forging is carried out at a change rate of from 20% to 60%,

wherein in the second cold rolling or the second cold forging, crystal grains is

crushed in a thickness direction to change a flat ratio of the crystal grains in a cross section orthogonal to a sputtering surface to be used for sputtering,

and wherein the heat treatment is carried out at a temperature of from 200 °C to 500 °C for 0.5 hours to 3 hours.

13. The method according to claim 12, wherein the first cold rolling or the first cold forging is carried out at a change rate of 70% or more.

14. The method according to claim 12 to 13, wherein the hot forging is carried out at a temperature of from 300 °C to 900 °C.

15. The method according to any one of claims 12 to 14, wherein the ingot contains one or more elements selected from the group consisting of Fe, Cr, Si, Ag, S, and P in a total amount of 0.01% by mass or less as the unavoidable impurities.

16. The method according to any one of claims 12 to 15, wherein the method manufactures a sputtering target containing 0.1% by mass to 6% by mass of at least one element selected from aluminum, manganese, nickel and cobalt.